

Dual N-Channel 40-V MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
40	0.016 at V _{GS} = 10 V	8	56
	0.019 at V _{GS} = 4.5 V	8	

FEATURES

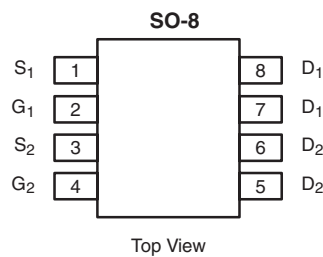
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- UIS Tested



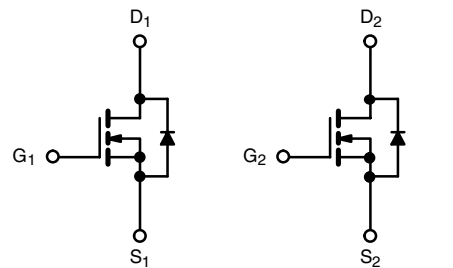
RoHS
COMPLIANT

APPLICATIONS

- CCFL Inverter



Ordering Information: Si4904DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	40	V	
Gate-Source Voltage	V _{GS}	± 16		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	8	
		T _C = 70 °C	8	
		T _A = 25 °C	8 ^{b, c}	
		T _A = 70 °C	6.5 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	20	A	
Source-Drain Current Diode Current	I _S	T _C = 25 °C		2.7
		T _A = 25 °C		1.6 ^{b, c}
Pulsed Source-Drain Current	I _{SM}	20		
Single Pulse Avalanche Current	I _{AS}	20		
Single Pulse Avalanche Energy	E _{AS}	20		
Maximum Power Dissipation	P _D	T _C = 25 °C	3.25	
		T _C = 70 °C	2.10	
		T _A = 25 °C	2.0 ^{b, c}	
		T _A = 70 °C	1.25 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ	Max	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	45	62.5	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	29	38		

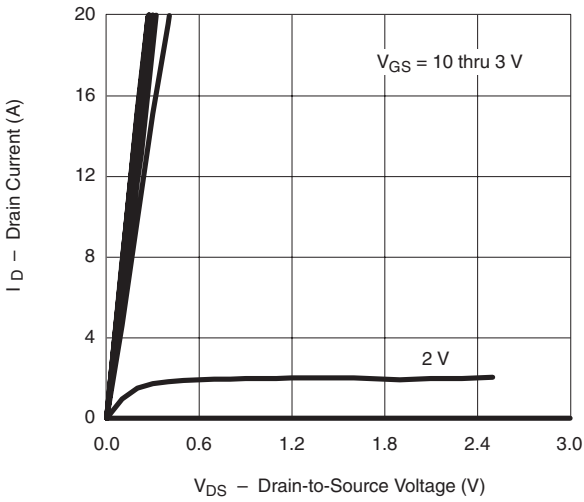
Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 Board.
- t = 10 s.
- Maximum under steady state conditions is 120 °C/W.

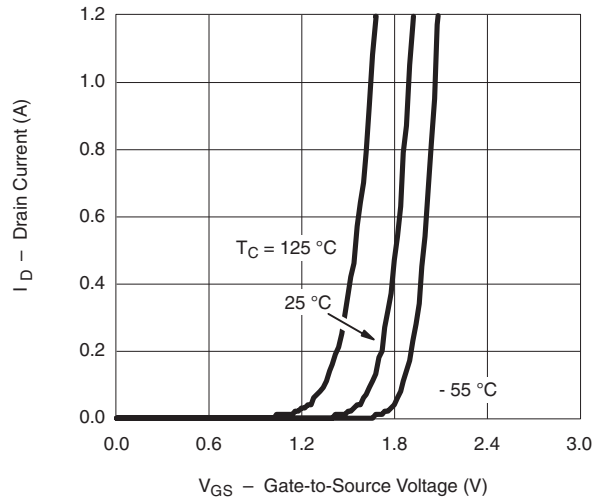
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		40		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$		- 4.8		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.8		2.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On -State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.013	0.016	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$		0.015	0.019	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		23		S
Dynamic^a						
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, I_D = 1\text{ MHz}$		2390		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			165		
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		56	85	nC
		N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		26	40	
Gate-Source Charge	Q_{gs}			5.5		
Gate-Drain Charge	Q_{gd}		9.7			
Gate Resistance	R_g	$f = 1\text{ MHz}$		2.6	4.0	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 1\text{ }\Omega$		15	23	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			56	85	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 1\text{ }\Omega$		88	135	
Rise Time	t_r			117	180	
Turn-Off Delay Time	$t_{d(off)}$			62	95	
Fall Time	t_f			19	30	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			2.7	A
Pulse Diode Forward Current ^a	I_{SM}				20	
Body Diode Voltage	V_{SD}	$I_S = 1.5\text{ A}$		0.69	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		62	95	ns
Body Diode Reverse Recovery Charge	Q_{rr}			62	95	nC
Reverse Recovery Fall Time	t_a			26		nS
Reverse Recovery Rise Time	t_b			36		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

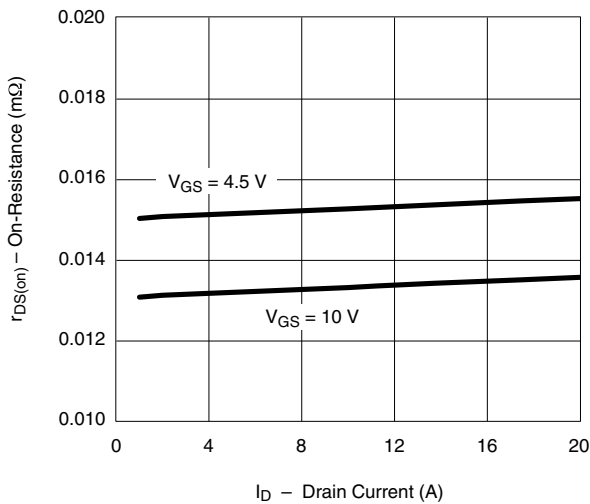
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



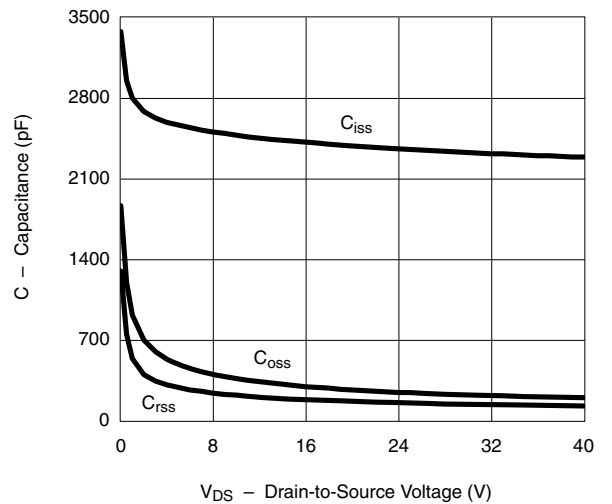
Output Characteristics



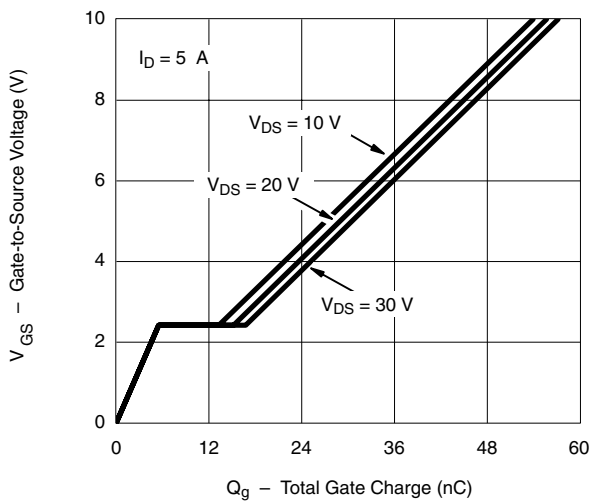
Transfer Characteristics



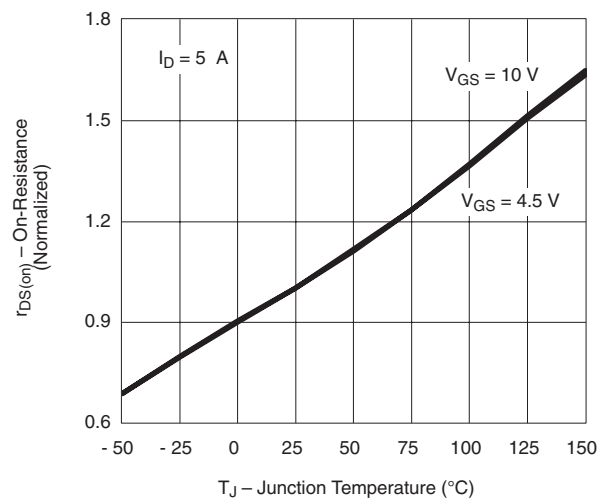
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

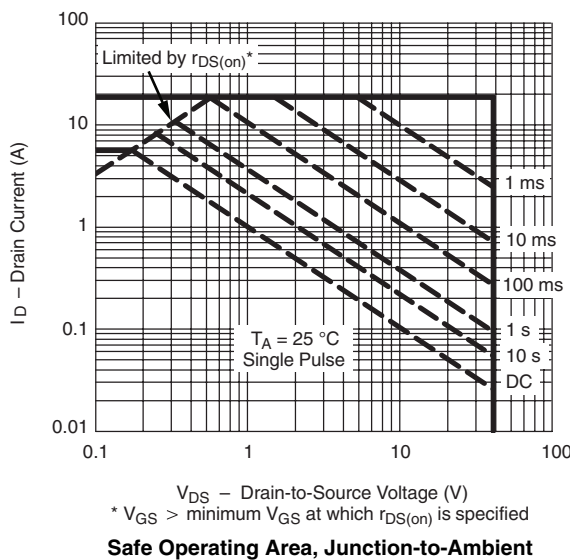
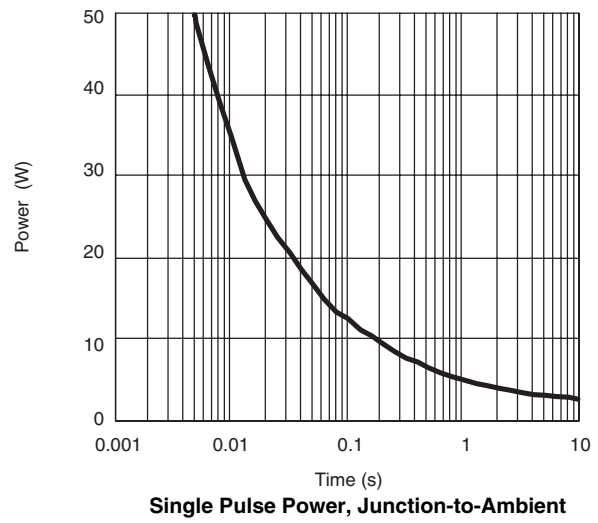
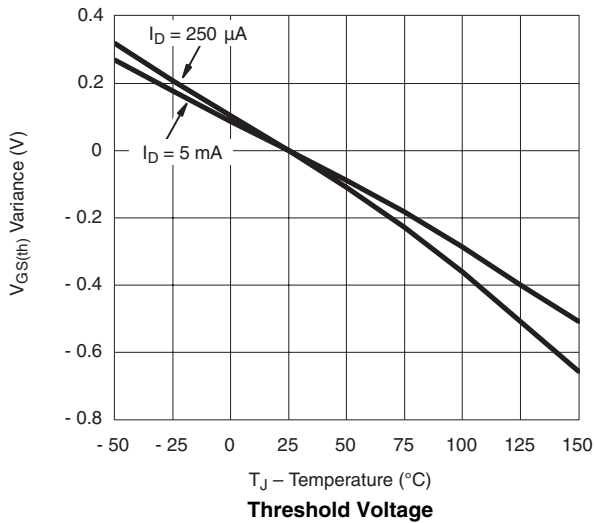
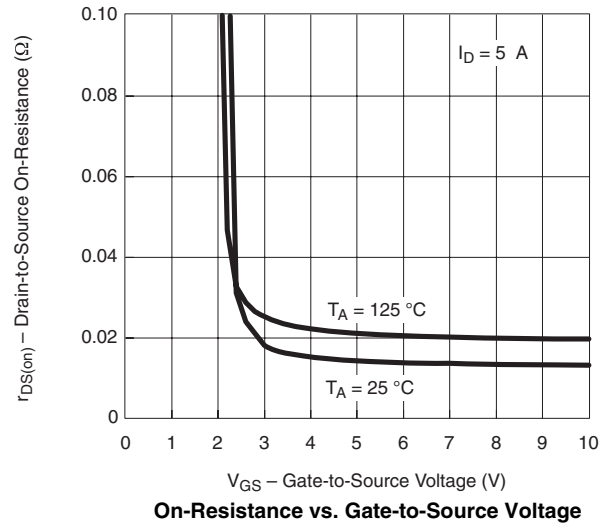
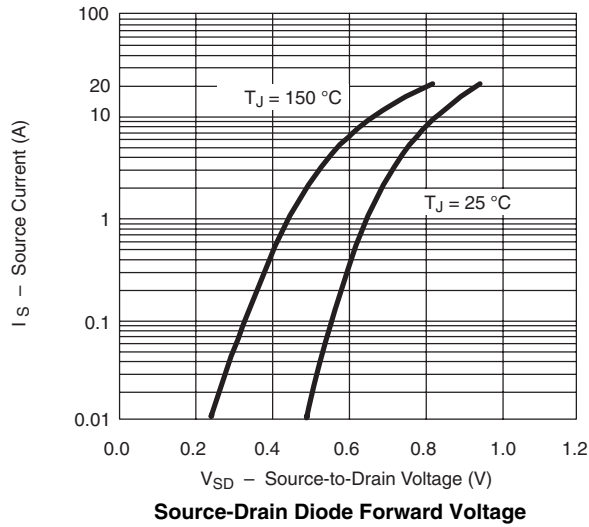


Gate Charge

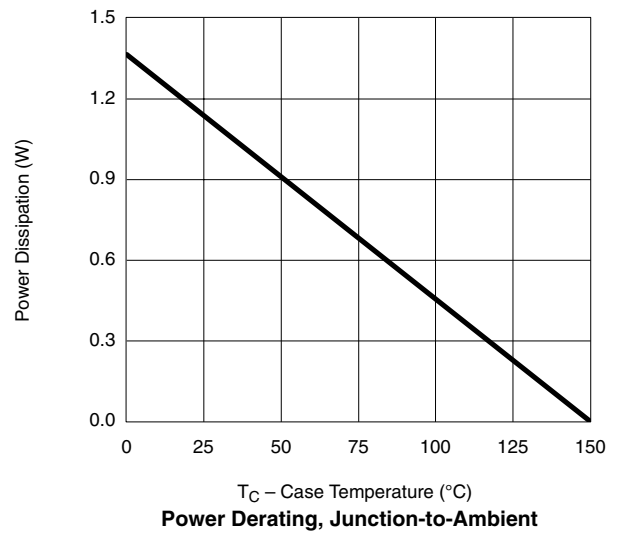
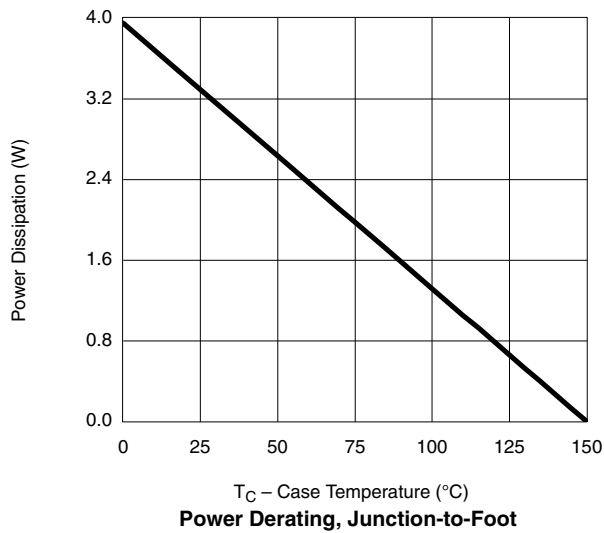
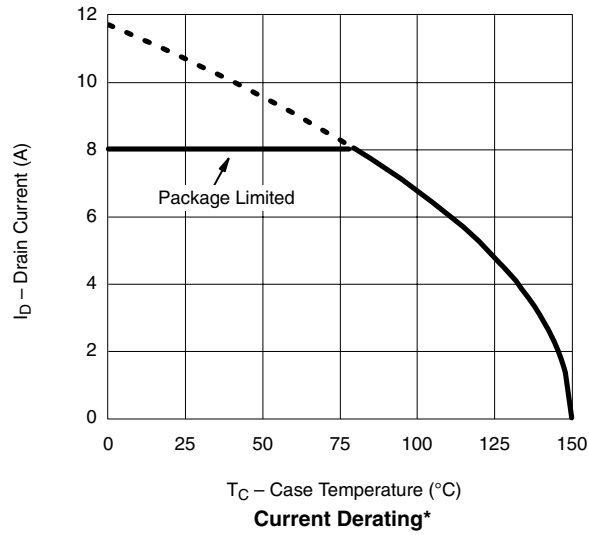


On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

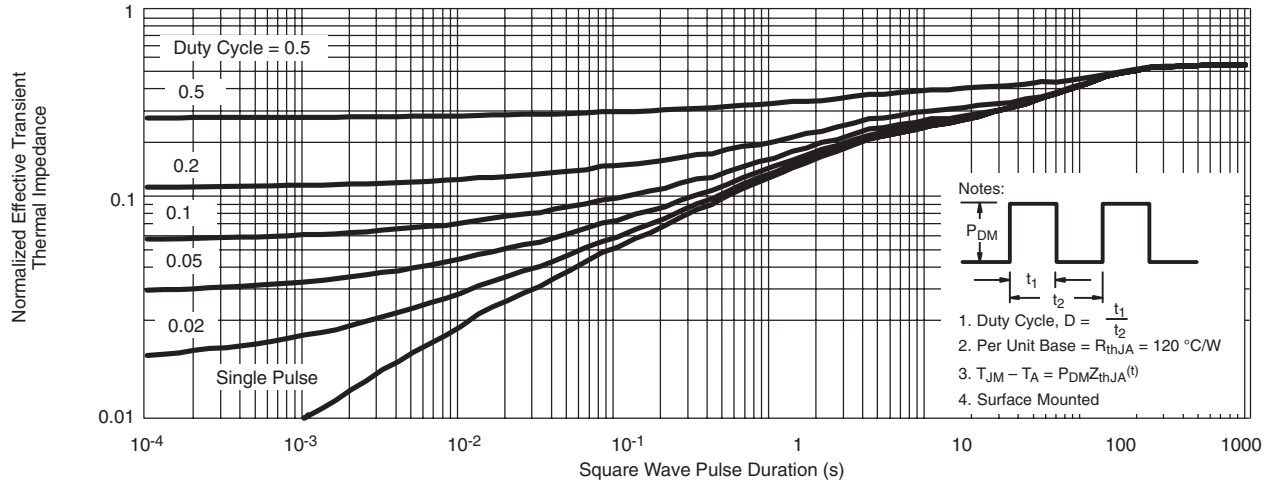


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

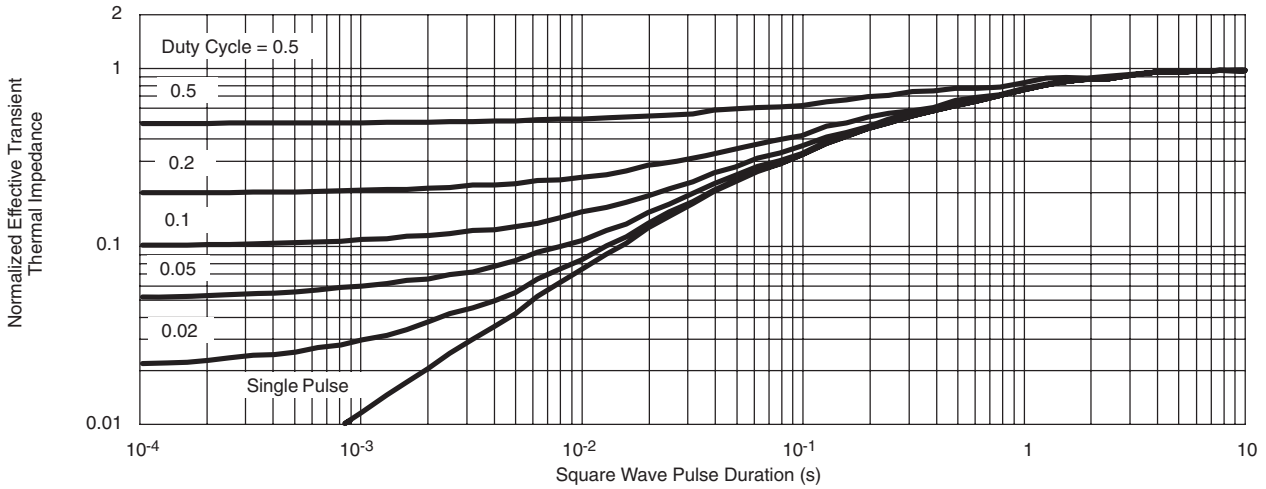


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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